

Si552 **REVISION D**

DUAL FREQUENCY VOLTAGE-CONTROLLED CRYSTAL OSCILLATOR (VCXO) 10 MHz TO 1.4 GHz

Internal fixed crystal frequency

 Available CMOS, LVPECL, LVDS, and CML outputs

Industry-standard 5 x 7 mm

package and pinout

Pb-free/RoHS-compliant

Low-jitter clock generation

Clock and data recovery

Optical modules

aging

ensures high reliability and low

Features

- Available with any-rate output frequencies from 10–945 MHz and selected frequencies to 1.4 GHz
- Two selectable output frequencies
- 3rd generation DSPLL[®] with superior jitter performance
- 3x better frequency stability than SAW-based oscillators

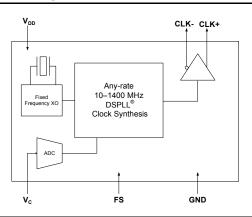
Applications

- SONET/SDH
- **xDSL**
- 10 GbE LAN/WAN

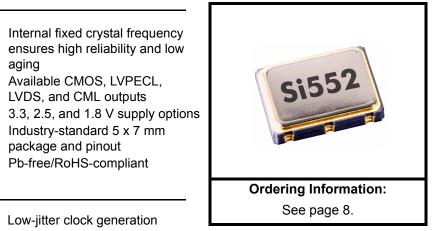
Description

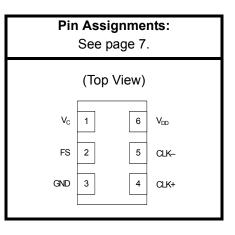
The Si552 dual-frequency VCXO utilizes Silicon Laboratories' advanced DSPLL[®] circuitry to provide a very low jitter clock for all output frequencies. The Si552 is available with anv-rate output frequency from 10 to 945 MHz and selected frequencies to 1400 MHz. Unlike traditional VCXOs, where a different crystal is required for each output frequency, the Si552 uses one fixed crystal frequency to provide a wide range of output frequencies. This IC-based approach allows the crystal resonator to provide exceptional frequency stability and reliability. In addition, DSPLL clock synthesis provides superior supply noise rejection, simplifying the task of generating low-jitter clocks in noisy environments typically found in communication systems. The Si552 IC-based VCXO is factory-configurable for a wide variety of user specifications including frequency, supply voltage, output format, tuning slope, and temperature stability. Specific configurations are factory programmed at time of shipment, thereby eliminating the long lead times associated with custom oscillators.

Functional Block Diagram



Rev. 0.6 6/07





1. Electrical Specifications

Table 1. Recommended Operating Conditions

| Parameter | Symbol | Test Condition | Min | Тур | Мах | Units |
|------------------------------------|-----------------|-----------------|------------------------|-----|------|-------|
| Supply Voltage ¹ | V _{DD} | 3.3 V option | 2.97 | 3.3 | 3.63 | |
| | | 2.5 V option | 2.25 | 2.5 | 2.75 | V |
| | | 1.8 V option | 1.71 | 1.8 | 1.89 | |
| Supply Current | I _{DD} | Output enabled | | | | |
| | | LVPECL | _ | 120 | 130 | |
| | | CML | _ | 108 | 117 | |
| | | LVDS | _ | 99 | 108 | mA |
| | | CMOS | _ | 90 | 98 | |
| | | Tristate mode | _ | 60 | 75 | |
| Frequency Select (FS) ² | | V _{IH} | 0.75 x V _{DD} | — | — | V |
| | | V _{IL} | — | _ | 0.5 | |
| Operating Temperature Range | T _A | | -40 | _ | 85 | °C |

1. Selectable parameter specified by part number. See Section 3. "Ordering Information" on page 8 for further details.

2. FS pin includes a 17 k Ω resistor to VDD.

Table 2. V_C Control Voltage Input

| Parameter | Symbol | Test Condition | Min | Тур | Max | Units |
|-----------------------------------------------|-------------------|------------------------------|-----|--------------------|-----------------|-------|
| Control Voltage Tuning Slope ^{1,2,3} | K _V | 10 to 90% of V _{DD} | — | 33 | _ | ppm/V |
| | | | | 45 | | |
| | | | | 90 | | |
| | | | | 135 | | |
| | | | | 180 | | |
| | | | | 356 | | |
| Control Voltage Linearity ⁴ | L _{VC} | BSL | -5 | ±1 | +5 | % |
| | | Incremental | -10 | ±5 | +10 | /0 |
| Modulation Bandwidth | BW | | 9.3 | 10.0 | 10.7 | kHz |
| V _C Input Impedance | Z _{VC} | | 500 | | | kΩ |
| Nominal Control Voltage | V _{CNOM} | @ f _O | — | V _{DD} /2 | | V |
| Control Voltage Tuning Range | V _C | | 0 | | V _{DD} | V |

Notes:

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1. Positive slope; selectable option by part number. See Section 3. "Ordering Information" on page 8.

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.

3. K_V variation is ±10% of typical values.

4. BSL determined from deviation from best straight line fit with V_C ranging from 10 to 90% of V_{DD} . Incremental slope determined with V_C ranging from 10 to 90% of V_{DD} .



Table 3. CLK± Output Frequency Characteristics

| Parameter | Symbol | Test Condition | Min | Тур | Мах | Units |
|--------------------------------------|------------------|------------------------------------|------|-----|------|-------|
| Nominal Frequency ^{1,2,3} | f _O | LVDS/CML/LVPECL | 10 | _ | 945 | MHz |
| | | CMOS | 10 | | 160 | |
| Temperature Stability ^{1,4} | | T _A = -40 to +85 °C | -20 | _ | +20 | |
| | | | -50 | — | +50 | ppm |
| | | | -100 | — | +100 | |
| Absolute Pull Range ^{1,4} | APR | | ±25 | _ | ±375 | ppm |
| Aging | | Frequency drift over first year. | | _ | ±3 | nnm |
| | | Frequency drift over 15 year life. | | _ | ±10 | - ppm |
| Power up Time ⁵ | t _{osc} | | | | 10 | ms |
| Settling Time After FS Change | t _{FRQ} | | _ | _ | 10 | ms |

Notes:

1. See Section 3. "Ordering Information" on page 8 for further details.

- 2. Specified at time of order by part number. Also available in frequencies from 970 to 1134 MHz and 1213 to 1417 MHz.
- **3.** Nominal output frequency set by $V_{CNOM} = V_{DD}/2$.
- 4. Selectable parameter specified by part number.
- **5.** Time from power up or tristate mode to f_O (to within ±1 ppm of f_O).

Table 4. CLK± Output Levels and Symmetry

| Symbol | Test Condition | Min | Тур | Max | Units |
|--------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------|
| V _O | mid-level | V _{DD} – 1.42 | _ | V _{DD} – 1.25 | V |
| V _{OD} | swing (diff) | 1.1 | | 1.9 | V _{PP} |
| V _{SE} | swing (single-ended) | 0.55 | | 0.95 | V _{PP} |
| V _O | mid-level | 1.125 | 1.20 | 1.275 | V |
| V _{OD} | swing (diff) | 0.5 | 0.7 | 0.9 | V_{PP} |
| V _O | mid-level | — | $V_{DD} - 0.75$ | — | V |
| V _{OD} | swing (diff) | 0.70 | 0.95 | 1.20 | V_{PP} |
| V _{OH} | I _{OH} = 32 mA | 0.8 x V _{DD} | _ | V _{DD} | V |
| V _{OL} | I _{OL} = 32 mA | — | | 0.4 | v |
| t _{R,} t _F | LVPECL/LVDS/CML | | _ | 350 | ps |
| | CMOS with C _L = 15 pF | — | 1 | — | ns |
| SYM | LVPECL: V _{DD} – 1.3 V (diff) LVDS: 1.25 V (diff) CMOS: V _{DD} /2 | 45 | | 55 | % |
| | V _O V _{OD} V _{SE} V _O V _{OD} V _{OD} V _{OD} V _{OH} V _{OL} | $\begin{tabular}{ c c c c } \hline V_O & mid-level \\ \hline V_{OD} & swing (diff) \\ \hline V_{SE} & swing (single-ended) \\ \hline V_O & mid-level \\ \hline V_{OD} & swing (diff) \\ \hline V_O & mid-level \\ \hline V_{OD} & swing (diff) \\ \hline V_{OH} & I_{OH} = 32 mA \\ \hline V_{OL} & I_{OL} = 32 mA \\ \hline V_{OL} & I_{OL} = 32 mA \\ \hline t_{R}, t_F & LVPECL/LVDS/CML \\ \hline CMOS with C_L = 15 pF \\ \hline SYM & LVPECL: & V_{DD} - 1.3 V (diff) \\ LVDS: & 1.25 V (diff) \\ \hline \end{array}$ | $\begin{tabular}{ c c c c c c } \hline V_O & mid-level & V_{DD}-1.42 \\ \hline V_{OD} & swing (diff) & 1.1 \\ \hline V_{SE} & swing (single-ended) & 0.55 \\ \hline V_O & mid-level & 1.125 \\ \hline V_{OD} & swing (diff) & 0.5 \\ \hline V_O & mid-level & \\ \hline V_{OD} & swing (diff) & 0.70 \\ \hline V_{OH} & I_{OH} = 32 \text{mA} & 0.8 \text{x} \text{V}_{DD} \\ \hline V_{OL} & I_{OL} = 32 \text{mA} & \\ \hline t_{R,} t_F & LVPECL/LVDS/CML & \\ \hline CMOS with C_L = 15 \text{pF} & \\ \hline SYM & LVPECL: V_{DD} - 1.3 \text{V} (diff) \\ LVDS: & 1.25 \text{V} (diff) & 45 \\ \hline \end{tabular}$ | $\begin{tabular}{ c c c c c c c } \hline V_O & mid-level & V_{DD}-1.42 & \\ \hline V_{OD} & swing (diff) & 1.1 & \\ \hline V_{SE} & swing (single-ended) & 0.55 & \\ \hline V_O & mid-level & 1.125 & 1.20 \\ \hline V_{OD} & swing (diff) & 0.5 & 0.7 \\ \hline V_O & mid-level & & V_{DD}-0.75 \\ \hline V_{OD} & swing (diff) & 0.70 & 0.95 \\ \hline V_{OD} & swing (diff) & 0.70 & 0.95 \\ \hline V_{OL} & I_{OL} = 32 \text{ mA} & 0.8 \text{ x } V_{DD} & \\ \hline V_{OL} & I_{OL} = 32 \text{ mA} & & \\ \hline t_{R,} t_F & LVPECL/LVDS/CML & & \\ \hline CMOS \text{ with } C_L = 15 \text{ pF} & & 1 \\ \hline SYM & LVPECL: & V_{DD} - 1.3 \text{ V } (diff) \\ LVDS: & 1.25 \text{ V } (diff) & 45 & \\ \hline \end{tabular}$ | $\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$ |

1. 50 Ω to V_{DD} – 2.0 V. **2.** R_{term} = 100 Ω (differential).

3. $C_L = 15 \, \text{pF}$



Table 5. CLK± Output Phase Jitter

| Parameter | Symbol | Test Condition | Min | Тур | Мах | Units |
|-------------------------------------|--------|---------------------------|-----|------|-----|-------|
| Phase Jitter (RMS) ^{1,2,3} | фJ | Kv = 33 ppm/V | | | | ps |
| for F _{OUT} ≥ 500 MHz | | 12 kHz to 20 MHz (OC-48) | _ | 0.26 | — | - |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.26 | — | |
| | | Kv = 45 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.27 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.26 | — | |
| | | Kv = 90 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.32 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.26 | — | |
| | | Kv = 135 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.40 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.27 | — | |
| | | Kv = 180 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.49 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.28 | — | |
| | | Kv = 356 ppm/V | | | | 1 |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.87 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.33 | — | |

Notes:

1. Differential Modes: LVPECL/LVDS/CML. Refer to AN255, AN256, and AN266 for further information.

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.
 See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply

rejection (PSR) advantage of Si55x versus SAW-based solutions.



Table 5. CLK± Output Phase Jitter (Continued)

| Parameter | Symbol | Test Condition | Min | Тур | Max | Units |
|----------------------------------------|--------|---------------------------|-----|------|-----|-------|
| Phase Jitter (RMS) ^{1,2,3} | фj | Kv = 33 ppm/V | | | | ps |
| for F _{OUT} of 125 to 500 MHz | | 12 kHz to 20 MHz (OC-48) | _ | 0.37 | — | |
| | | 50 kHz to 80 MHz (OC-192) | _ | 0.33 | — | |
| | | Kv = 45 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | _ | 0.37 | _ | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.33 | — | |
| | | Kv = 90 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | _ | 0.43 | _ | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.34 | — | |
| | | Kv = 135 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | — | 0.50 | — | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.34 | — | |
| | | Kv = 180 ppm/V | | | | |
| | | 12 kHz to 20 MHz (OC-48) | _ | 0.59 | _ | |
| | | 50 kHz to 80 MHz (OC-192) | — | 0.35 | — | |
| | | Kv = 356 ppm/V | | | | 1 |
| | | 12 kHz to 20 MHz (OC-48) | _ | 1.00 | | |
| | | 50 kHz to 80 MHz (OC-192) | _ | 0.39 | — | |

Notes:

1. Differential Modes: LVPECL/LVDS/CML. Refer to AN255, AN256, and AN266 for further information.

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.

3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.

Table 6. CLK± Output Period Jitter

| Parameter | Symbol | Test Condition | Min | Тур | Max | Units | |
|---------------------------------------------------------------------------------------------------------------------|------------------|----------------|-----|-----|-----|-------|--|
| Period Jitter* | J _{PER} | RMS | _ | 2 | — | ps | |
| | | Peak-to-Peak | | 14 | — | | |
| *Note: Any output mode, including CMOS, LVPECL, LVDS, CML. N = 1000 cycles. Refer to AN279 for further information. | | | | | | | |



| Offset Frequency | 74.25 MHz 90 ppm/V | 491.52 MHz 45 ppm/V | 622.08 MHz 135 ppm/V | Units |
|------------------|-----------------------|------------------------|-------------------------|--------|
| | LVPECL | LVPECL | LVPECL | |
| 100 Hz | -87 | -75 | -65 | |
| 1 kHz | -114 | -100 | -90 | |
| 10 kHz | -132 | -116 | -109 | |
| 100 kHz | -142 | -124 | -121 | dBc/Hz |
| 1 MHz | -148 | -135 | -134 | |
| 10 MHz | -150 | -146 | -146 | |
| 100 MHz | n/a | -147 | -147 | |

Table 7. CLK± Output Phase Noise (Typical)

Table 8. Absolute Maximum Ratings¹

| Parameter | Symbol | Rating | Units |
|-------------------------------------------------------------------------------|-------------------|-------------------------------|---------|
| Maximum Operating Temperature | T _{AMAX} | 85 | °C |
| Supply Voltage | V _{DD} | -0.5 to +3.8 | Volts |
| Input Voltage (any input pin) | VI | -0.5 to V _{DD} + 0.3 | Volts |
| Storage Temperature | Τ _S | -55 to +125 | °C |
| ESD Sensitivity (HBM, per JESD22-A114) | ESD | 2500 | Volts |
| Soldering Temperature (Pb-free profile) ² | T _{PEAK} | 260 | °C |
| Soldering Temperature Time @ T _{PEAK} (Pb-free profile) ² | t _P | 20–40 | seconds |
| | | 1 | |

Notes:

1. Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Functional operation or specification compliance is not implied at these conditions. Exposure to maximum rating conditions for extended periods may affect device reliability.

2. The device is compliant with JEDEC J-STD-020C. Refer to Si5xx Packaging FAQ available for download from www.silabs.com/VCXO for further information, including soldering profiles.

Table 9. Environmental Compliance

The Si552 meets the following qualification test requirements.

| Parameter | Conditions/Test Method |
|------------------------|-------------------------------|
| Mechanical Shock | MIL-STD-883F, Method 2002.3 B |
| Mechanical Vibration | MIL-STD-883F, Method 2007.3 A |
| Solderability | MIL-STD-883F, Method 203.8 |
| Gross & Fine Leak | MIL-STD-883F, Method 1014.7 |
| Resistance to Solvents | MIL-STD-883F, Method 2016 |



2. Pin Descriptions

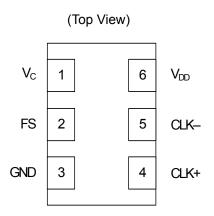


Table 10. Si552 Pin Descriptions

| Pin | Name | Туре | Function | | | | |
|-----|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|------------------------------------------------------------------------------------|--|--|--|--|
| 1 | V _C | Analog Input | Control Voltage | | | | |
| 2 | FS* | Input | Frequency Select: 0 = first frequency selected 1 = second frequency selected | | | | |
| 3 | GND | Ground | Electrical and Case Ground | | | | |
| 4 | CLK+ | Output | Oscillator Output | | | | |
| 5 | CLK– (N/A for CMOS) | Output | Complementary Output (N/C for CMOS) | | | | |
| 6 | V _{DD} | Power | Power Supply Voltage | | | | |
| | *Note: FS includes a 17 kΩ pullup resistor to V _{DD} . See Section 3. "Ordering Information" on page 8 for details on frequency select and OE polarity ordering options. | | | | | | |



3. Ordering Information

The Si552 supports a variety of options including frequency, temperature stability, tuning slope, output format, and V_{DD} . Specific device configurations are programmed into the Si552 at time of shipment. Configurations are specified using the Part Number Configuration chart shown below. Silicon Labs provides a web browser-based part number configuration utility to simplify this process. Refer to www.silabs.com/VCXOPartNumber to access this tool and for further ordering instructions. The Si552 VCXO series is supplied in an industry-standard, RoHS-compliant, lead-free, 6-pad, 5 x 7 mm package. Tape and reel packaging is an ordering option.

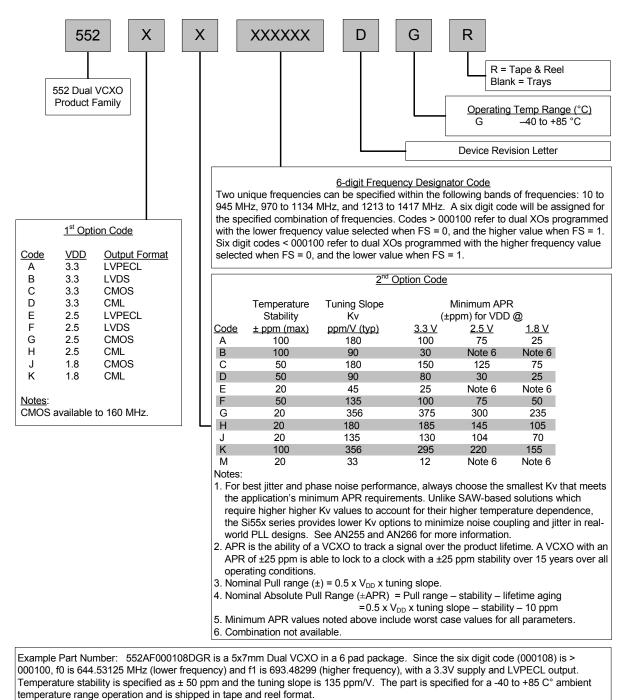


Figure 1. Part Number Convention



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4. Si55x Mark Specification

Figure 2 illustrates the mark specification for the Si552. Table 11 lists the line information.

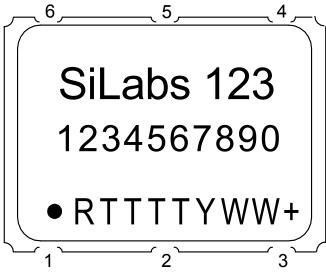


Figure 2. Mark Specification

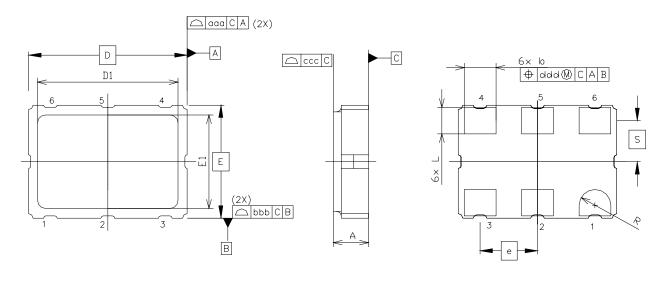
Table 11. Si55x Top Mark Description

| Line | Position | Description | | | | |
|------|--------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------|--|--|--|--|
| 1 | 1–10 | "SiLabs"+ Part Family Number, 5xx (First 3 characters in part number) | | | | |
| 2 | 1–10 | Si550: Option1+Option2+Freq(7)+Temp Si552, Si554, Si550 w/ 8-digit resolution: Option1+Option2+ConfigNum(6)+Ter | | | | |
| 3 | Trace Code | | | | | |
| | Position 1 | Pin 1 orientation mark (dot) | | | | |
| | Position 2 | Product Revision (D) | | | | |
| | Position 3–6 | Tiny Trace Code (4 alphanumeric characters per assembly release instructions) | | | | |
| | Position 7 | Year (least significant year digit), to be assigned by assembly site (ex: 2007 = 7) | | | | |
| | Position 8–9 Calendar Work Week number (1–53), to be assigned by assembly site | | | | | |
| | Position 10 | "+" to indicate Pb-Free and RoHS-compliant | | | | |



5. Outline Diagram and Suggested Pad Layout

Figure 3 illustrates the package details for the Si552. Table 12 lists the values for the dimensions shown in the illustration.



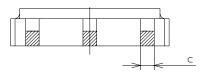


Figure 3. Si552 Outline Diagram

| Dimension | Min | Nom | Max |
|-----------|-----------|------|------|
| А | 1.45 | 1.65 | 1.85 |
| b | 1.2 | 1.4 | 1.6 |
| С | 0.60 TYP | | |
| D | 7.00 BSC | | |
| D1 | 6.10 | 6.2 | 6.30 |
| е | 2.54 BSC | | |
| E | 5.00 BSC | | |
| E1 | 4.30 | 4.40 | 4.50 |
| L | 1.07 | 1.27 | 1.47 |
| S | 1.815 BSC | | |
| R | 0.7 REF | | |
| aaa | — | | 0.15 |
| bbb | — | — | 0.15 |
| CCC | — | — | 0.10 |
| ddd | — | — | 0.10 |

Table 12. Package Diagram Dimensions (mm)



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6. 6-Pin PCB Land Pattern

Figure 4 illustrates the 6-pin PCB land pattern for the Si552. Table 13 lists the values for the dimensions shown in the illustration.

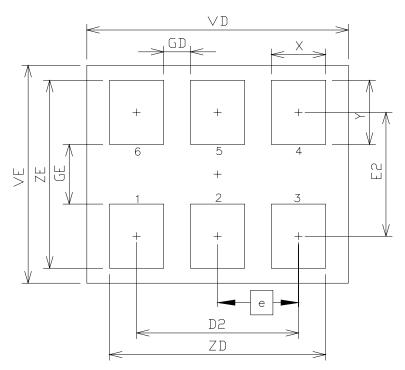


Figure 4. Si552 PCB Land Pattern

| Dimension | Min | Max | |
|-----------|----------|------|--|
| D2 | 5.08 REF | | |
| е | 2.54 BSC | | |
| E2 | 4.15 REF | | |
| GD | 0.84 | | |
| GE | 2.00 | | |
| VD | 8.20 REF | | |
| VE | 7.30 REF | | |
| Х | 1.70 TYP | | |
| Y | 2.15 | REF | |
| ZD | — | 6.78 | |
| ZE | | 6.30 | |

Table 13. PCB Land Pattern Dimensions (mm)

1. Dimensioning and tolerancing per the ANSI Y14.5M-1994 specification.

2. Land pattern design based on IPC-7351 guidelines.

3. All dimensions shown are at maximum material condition (MMC).

4. Controlling dimension is in millimeters (mm).



DOCUMENT CHANGE LIST

Revision 0.3 to Revision 0.4

- Updated Table 1, "Recommended Operating Conditions," on page 2.
 - Added maximum supply current specifications.
 - Specified relationship between temperature at startup and operation temperature.

Revision 0.4 to Revision 0.5

 Updated Note 3 in Table 1, "Recommended Operating Conditions," on page 2.

Revision 0.5 to Revision 0.6

- Updated Table 1, "Recommended Operating Conditions," on page 2.
 - Device maintains stable operation over -40 to +85 °C operating temperature range.
 - Supply current specifications updated for revision D.
- Updated Table 4, "CLK± Output Levels and Symmetry," on page 3.
 - Updated LVDS differential peak-peak swing specifications.
- Updated Table 5, "CLK± Output Phase Jitter," on page 4.
- Updated Table 6, "CLK± Output Period Jitter," on page 5.
 - Revised period jitter specifications.
- Updated Table 8, "Absolute Maximum Ratings¹," on page 6 to reflect the soldering temperature time at 260 °C is 20–40 sec per JEDEC J-STD-020C.
- Updated 3. "Ordering Information" on page 8.
 Changed ordering instructions to revision D.
- Added 4. "Si55x Mark Specification" on page 9.



NOTES:

CONTACT INFORMATION

Silicon Laboratories Inc.

400 West Cesar Chavez Austin, TX 78701 Tel: 1+(512) 416-8500 Fax: 1+(512) 416-9669 Toll Free: 1+(877) 444-3032

Email: VCXOinfo@silabs.com Internet: www.silabs.com

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